

FIG. 1

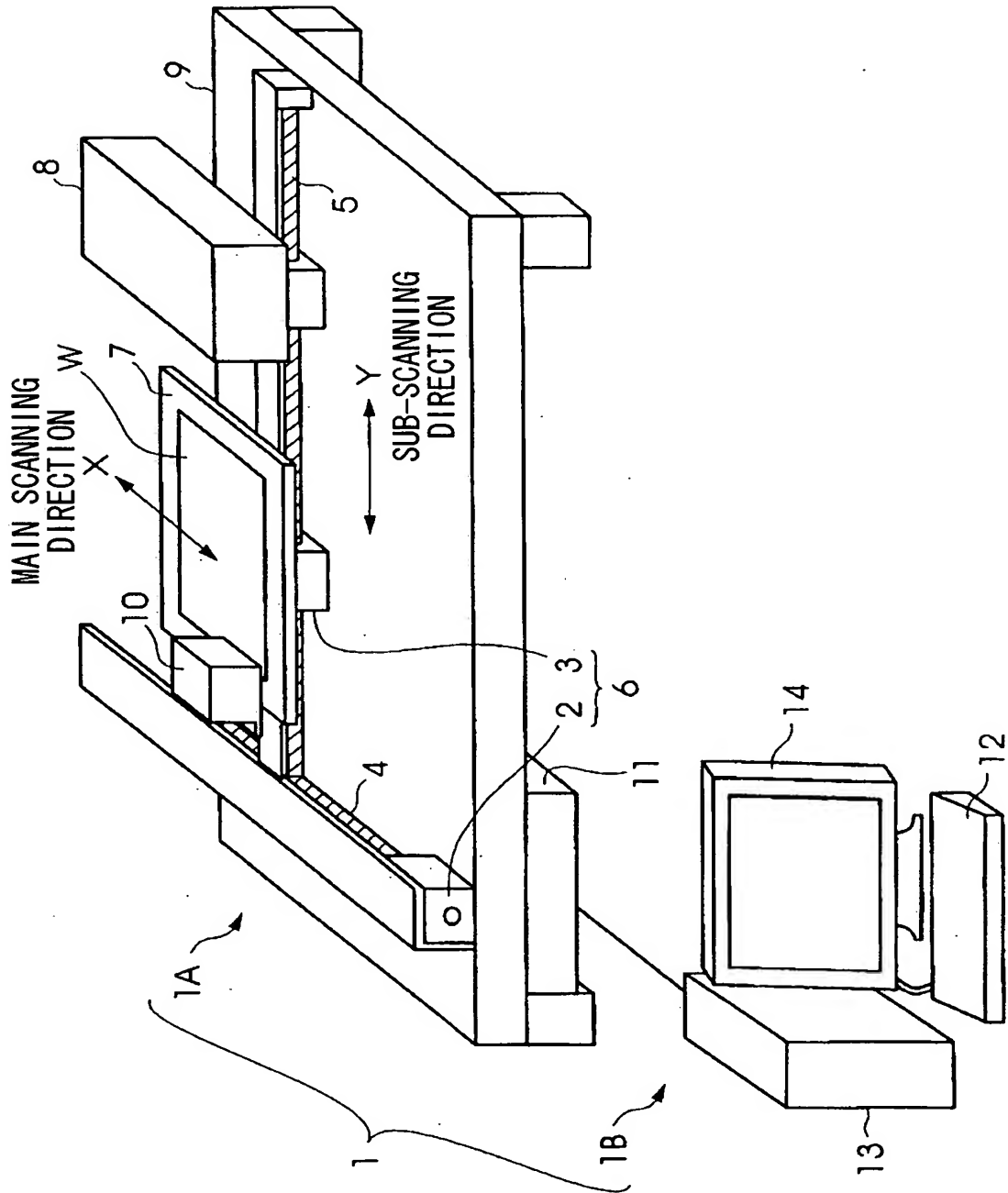


FIG. 2 22

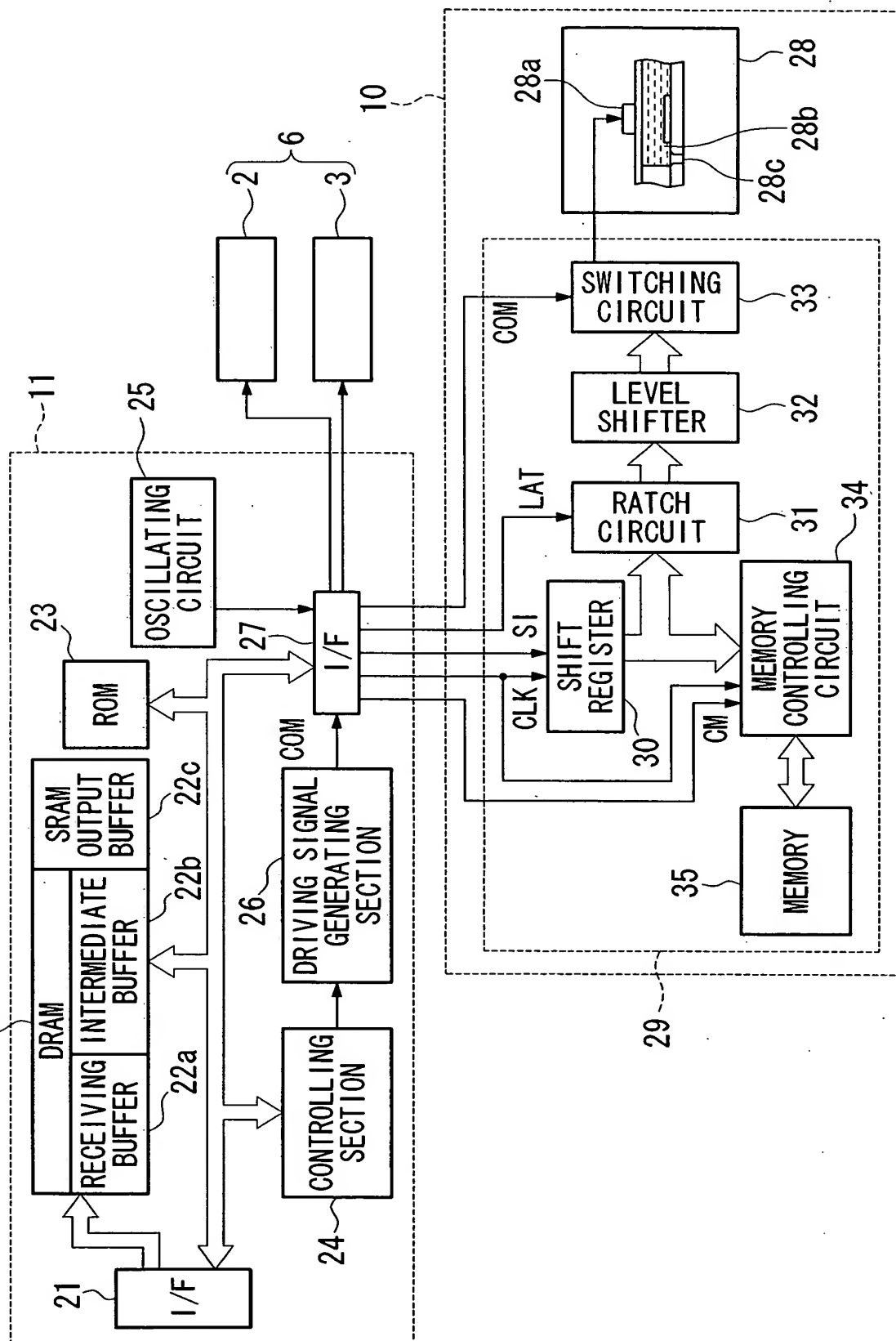


FIG. 3

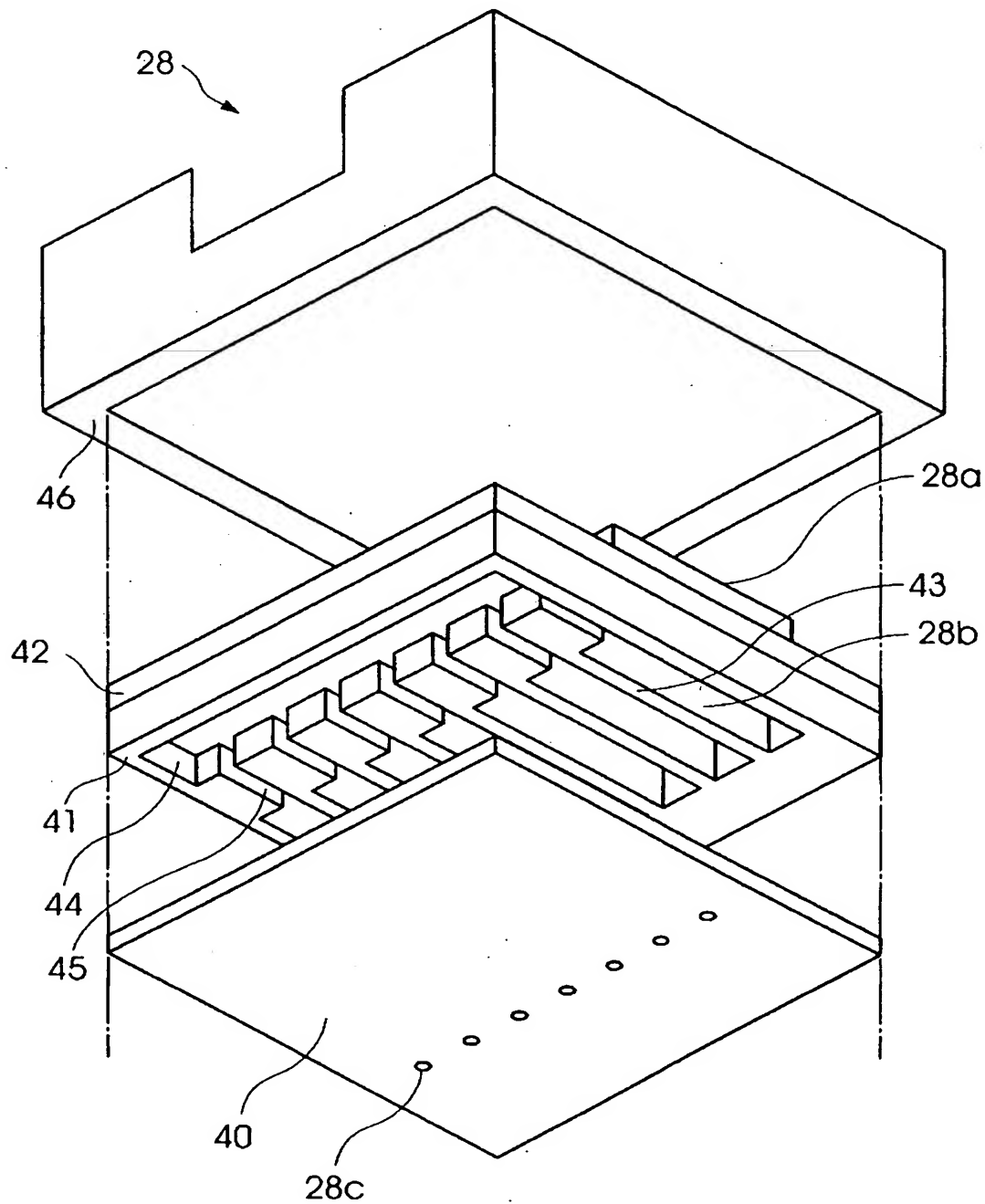


FIG. 1 is a cross-sectional view of a semiconductor device. The device is built on a substrate 40, which includes a base layer 42 and a middle layer 41. A central structure 28 is formed, consisting of a curved layer 28a, a central core 28b, and a base layer 28c. A vertical structure 46 is positioned to the right of the central structure. Other features are labeled 44 and 45.

FIG. 5A

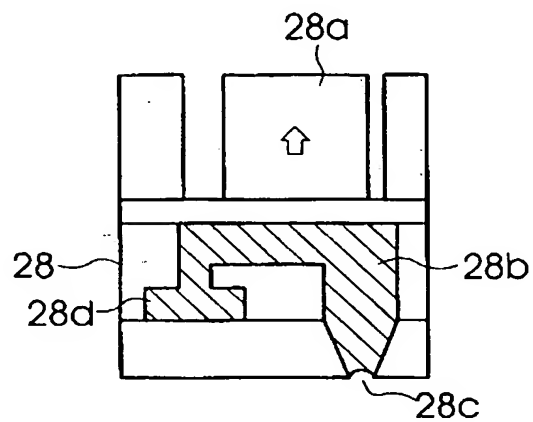


FIG. 5B

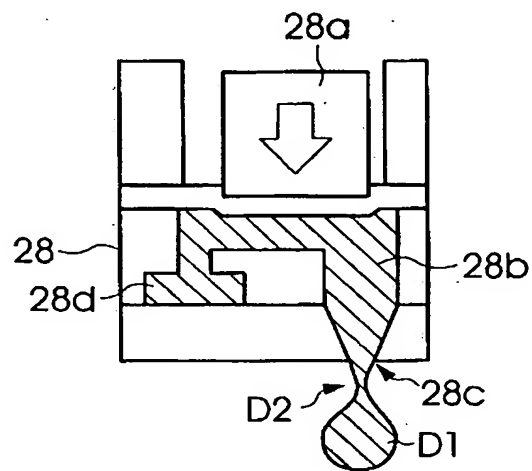


FIG. 5C

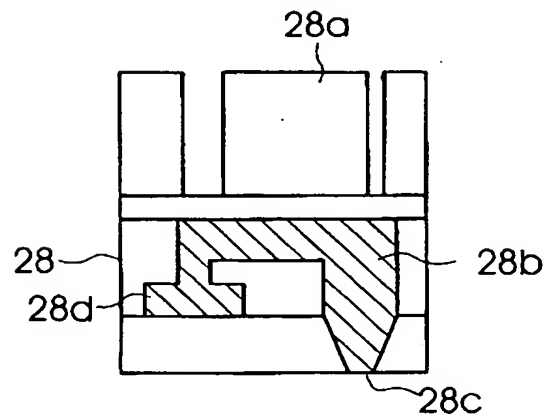


FIG. 6

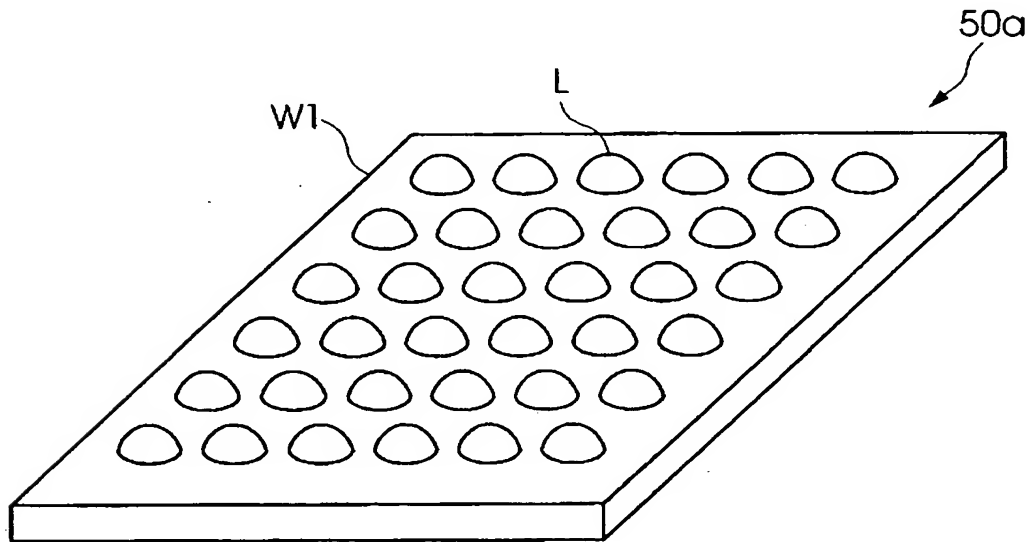


FIG. 7

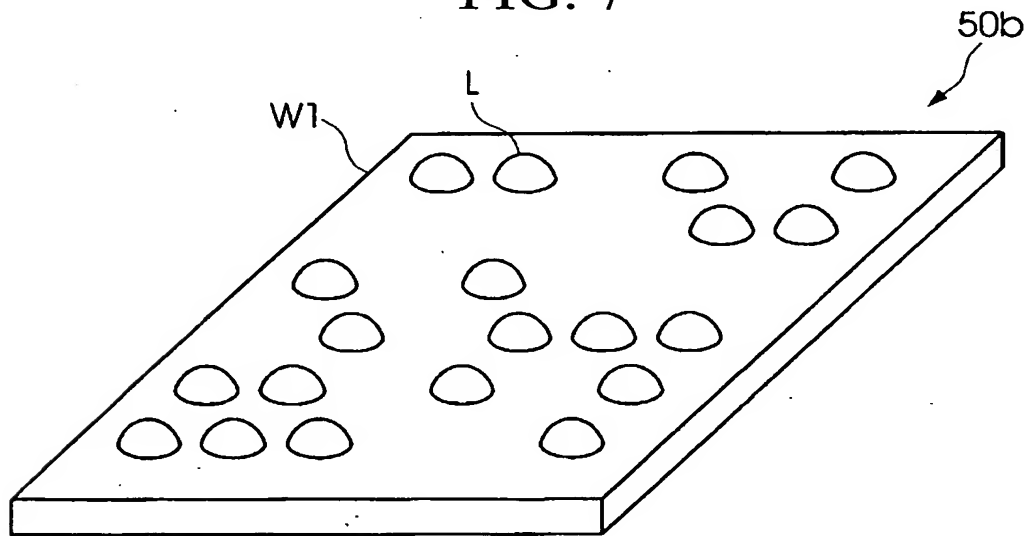


FIG. 8

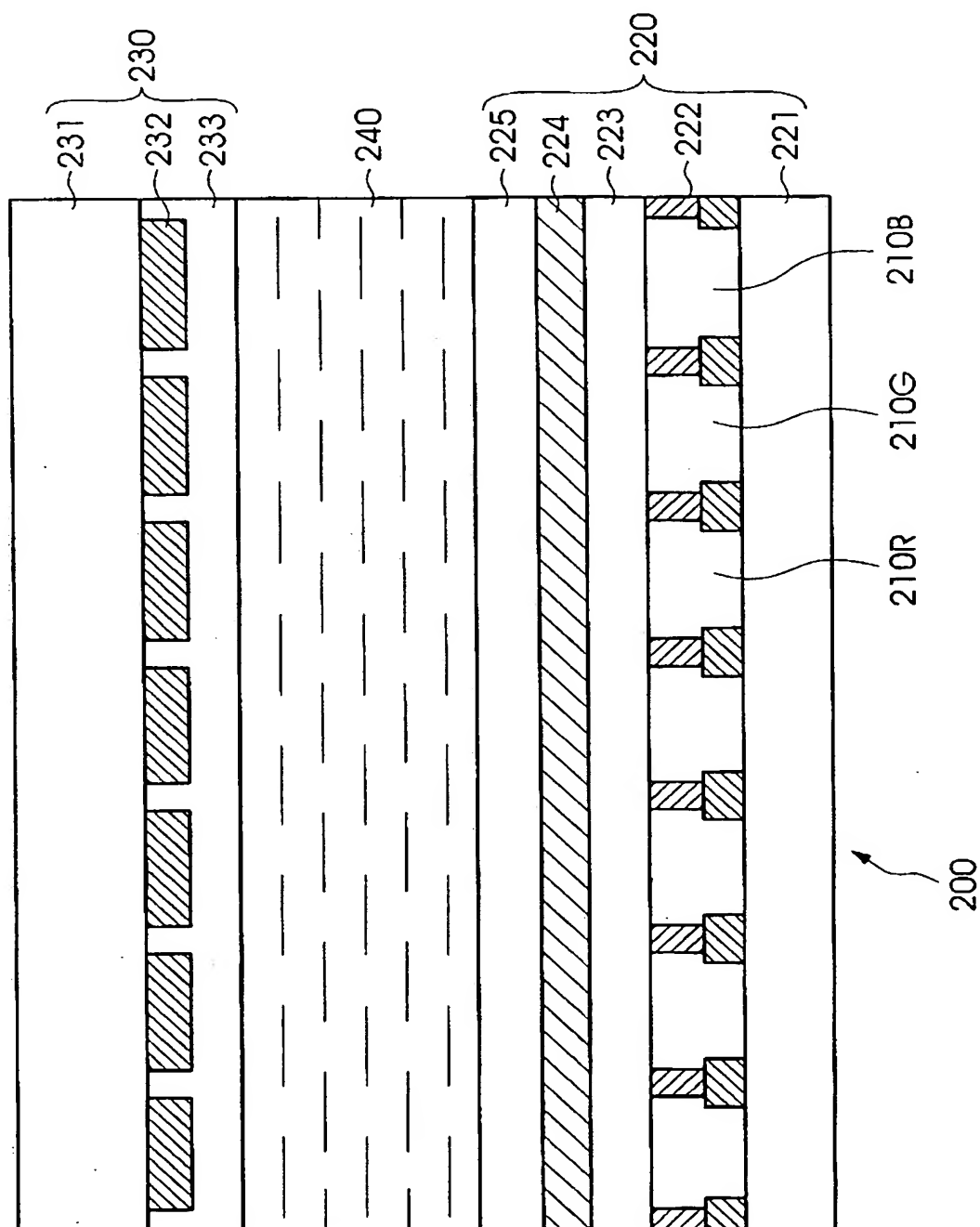






FIG. 10

